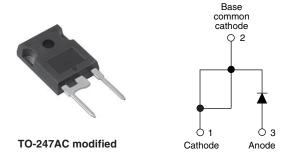
VS-30EPH06PbF, VS-30EPH06-N3

Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt®



PRIMARY CHARACTERISTICS						
I _{F(AV)}	30 A					
V_{R}	600 V					
V _F at I _F	1.34 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Package	TO-247AC modified					
Circuit configuration	Single					

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Single diode device
- Designed and qualified according to JEDEC®-JESD 47







RoHS

HALOGEN FREE Available

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V_{RRM}		600	V		
Average rectified forward current	I _{F(AV)}	T _C = 116 °C	30	А		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	300			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-			
Forward voltage	V _F	I _F = 30 A	-	2.0	2.6	V		
		I _F = 30 A, T _J = 150 °C	-	1.34	1.75			
D leal	1	$V_R = V_R$ rated	-	0.3	50			
Reverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	60	500	- μA		
Junction capacitance	C _T	V _R = 600 V	-	33	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	ı	3.5	-	nH		



VS-30EPH06PbF, VS-30EPH06-N3

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		28	35		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	31	-	ns	
		T _J = 125 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	77	-		
Peak recovery current	I _{RRM}	T _J = 25 °C		-	3.5	-	А	
		T _J = 125 °C		-	7.7	-	A	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	65	-	200	
		T _J = 125 °C		-	345	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	0.5	0.9		
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.4	-		
Weight			-	6.0	-	g	
Weight			-	0.22	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC modified		30EPH06			

www.vishay.com

Vishay Semiconductors

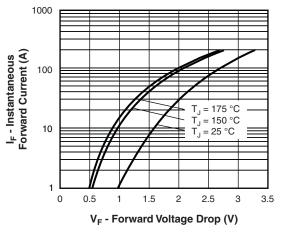


Fig. 1 - Typical Forward Voltage Drop Characteristics

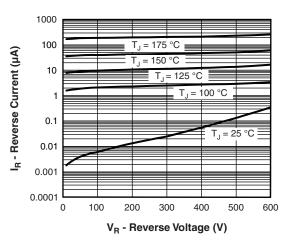


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

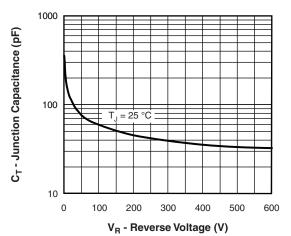


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

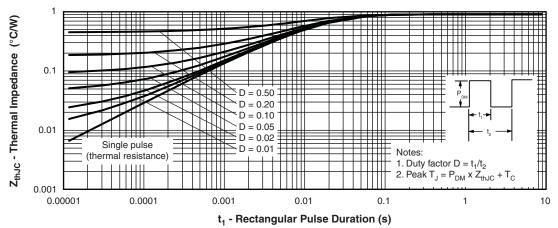


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Vishay Semiconductors

Allowable Case Temperature (°C)

www.vishay.com

180 160 140 Square wave (D = 0.50) Rated V_R applied 100 See note (1) 80 0 5 10 15 20 25 30 35 40 45 I_{F(AV)} - Average Forward Current (A)

Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

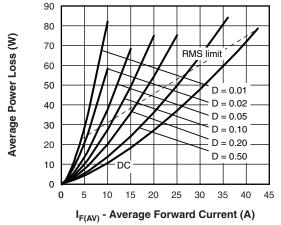


Fig. 6 - Forward Power Loss Characteristics

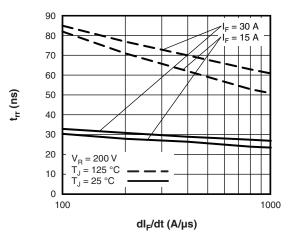


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

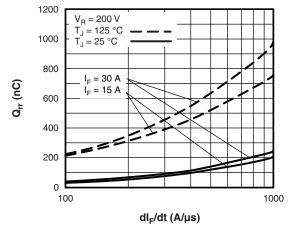


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

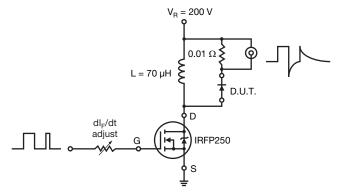
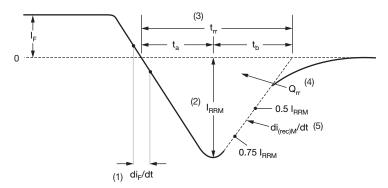


Fig. 9 - Reverse Recovery Parameter Test Circuit

www.vishay.com

Vishay Semiconductors



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

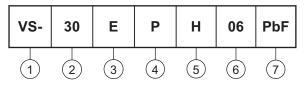
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- Current rating (30 = 30 A)
- Circuit configuration: E = single diode

Package:

P = TO-247AC modified

H = hyperfast recovery

Voltage rating (06 = 600 V)

Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-30EPH06PbF	25	500	Antistatic plastic tube			
VS-30EPH06-N3	25	500	Antistatic plastic tube			

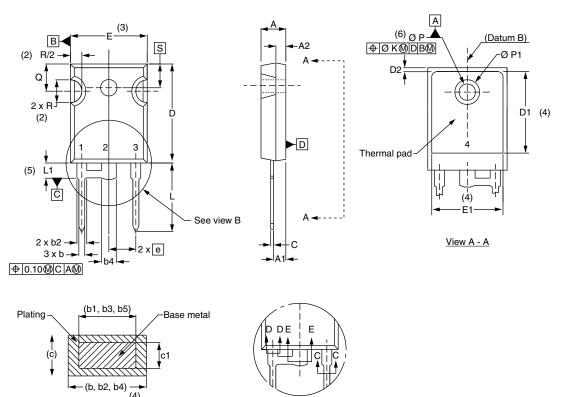
LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95541			
But and in information	TO-247AC modified PbF	www.vishay.com/doc?95255			
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442			
SPICE model		www.vishay.com/doc?96573			



Vishay Semiconductors

TO-247AC modified - 50 mils L/F

DIMENSIONS in millimeters and inches



View B

SYMBOL	MILLIM	IETERS	INCHES		NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

Section C - C, D - D, E - E

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	BSC	
ØK	0.254		0.0	0.010	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217	BSC	

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.